



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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IGBT Modules

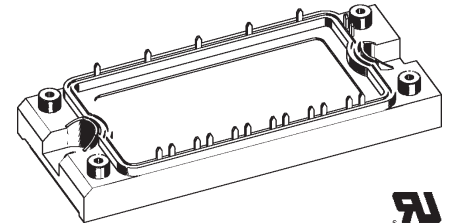
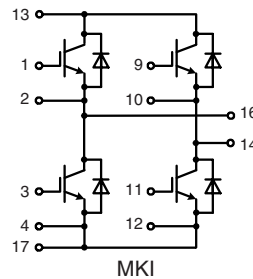
H Bridge

Short Circuit SOA Capability
Square RBSOA

$$I_{C25} = 65 \text{ A}$$

$$V_{CES} = 1200 \text{ V}$$

$$V_{CE(sat) \text{ typ.}} = 3.2 \text{ V}$$



IGBTs		
Symbol	Conditions	Maximum Ratings
V_{CES}	$T_{VJ} = 25^{\circ}\text{C}$ to 150°C	1200 V
V_{GES}		± 20 V
I_{C25}	$T_C = 25^{\circ}\text{C}$	65 A
I_{C80}	$T_C = 80^{\circ}\text{C}$	45 A
I_{CM}	$V_{GE} = \pm 15 \text{ V}$; $R_G = 13 \Omega$; $T_{VJ} = 125^{\circ}\text{C}$	100 A
V_{CEK}	RBSOA; clamped inductive load; $L = 100 \mu\text{H}$	V_{CES}
t_{SC}	$V_{CE} = 900 \text{ V}$; $V_{GE} = \pm 15 \text{ V}$; $R_G = 13 \Omega$; $T_{VJ} = 125^{\circ}\text{C}$ SCSOA; non-repetitive	10 μs
P_{tot}	$T_C = 25^{\circ}\text{C}$	350 W

Features

- Fast NPT IGBTs
 - low saturation voltage
 - positive temperature coefficient for easy paralleling
 - fast switching
 - short tail current for optimized performance also in resonant circuits
- HiPerFRED™ diode:
 - fast reverse recovery
 - low operating forward voltage
 - low leakage current
- Industry Standard Package
 - solderable pins for PCB mounting
 - isolated copper base plate
 - UL registered, E 72873

Symbol	Conditions	Characteristic Values ($T_{VJ} = 25^{\circ}\text{C}$, unless otherwise specified)			
		min.	typ.	max.	
$V_{CE(sat)}$	$I_C = 50 \text{ A}$; $V_{GE} = 15 \text{ V}$; $T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		3.2 3.8	V V	
$V_{GE(th)}$	$I_C = 2 \text{ mA}$; $V_{GE} = V_{CE}$	4.5		6.5 V	
I_{CES}	$V_{CE} = V_{CES}$; $V_{GE} = 0 \text{ V}$; $T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		2.5	0.7 mA mA	
I_{GES}	$V_{CE} = 0 \text{ V}$; $V_{GE} = \pm 20 \text{ V}$			500 nA	
$t_{d(on)}$ t_r $t_{d(off)}$ t_f E_{on} E_{off}	Inductive load, $T_{VJ} = 125^{\circ}\text{C}$ $V_{CE} = 600 \text{ V}$; $I_C = 50 \text{ A}$ $V_{GE} = \pm 15 \text{ V}$; $R_G = 13 \Omega$		130 60 360 30 6.0 2.5	ns ns ns ns mJ mJ	
C_{ies}		$V_{CE} = 25 \text{ V}$; $V_{GE} = 0 \text{ V}$; $f = 1 \text{ MHz}$		3.3	nF
Q_{Gon}		$V_{CE} = 600 \text{ V}$; $V_{GE} = 15 \text{ V}$; $I_C = 50 \text{ A}$		600	nC
R_{thJC}		(per IGBT)			0.35 KW

Typical Applications

- motor control
 - . DC motor amature winding
 - . DC motor excitation winding
 - . synchronous motor excitation winding
- supply of transformer primary winding
 - . power supplies
 - . welding
 - . X-ray
 - . battery charger

Diodes

Symbol	Conditions	Maximum Ratings	
I_{F25}	$T_C = 25^\circ\text{C}$	110	A
I_{F80}	$T_C = 80^\circ\text{C}$	70	A

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
V_F	$I_F = 50\text{ A}; V_{GE} = 0\text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	2.2	2.6	V
I_{RM} t_{rr}	$I_F = 50\text{ A}; di_F/dt = -500\text{ A}/\mu\text{s}; T_{VJ} = 125^\circ\text{C}$ $V_R = 600\text{ V}; V_{GE} = 0\text{ V}$	40		A
		200		ns
R_{thJC}	(per diode)			0.61 K/W

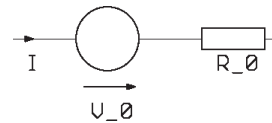
Module

Symbol	Conditions	Maximum Ratings	
T_{VJ}	operating	-40...+125	$^\circ\text{C}$
T_{VJM}		-40...+150	$^\circ\text{C}$
T_{stg}		-40...+125	$^\circ\text{C}$
V_{ISOL}	$I_{ISOL} \leq 1\text{ mA}; 50/60\text{ Hz}$	2500	V~
M_d	Mounting torque (M5)	2.7 - 3.3	Nm

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$R_{pin-chip}$			5	m Ω
d_S	Creepage distance on surface	6		mm
d_A	Strike distance in air	6		mm
R_{thCH}	with heatsink compound		0.02	K/W
Weight			180	g

Equivalent Circuits for Simulation

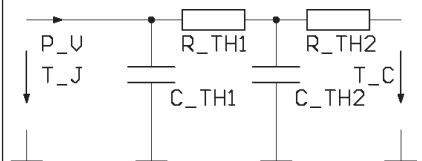
Conduction



IGBT (typ. at $V_{GE} = 15\text{ V}; T_J = 125^\circ\text{C}$)
 $V_0 = 2.05\text{ V}; R_0 = 35\text{ m}\Omega$

Free Wheeling Diode (typ. at $T_J = 125^\circ\text{C}$)
 $V_0 = 1.3\text{ V}; R_0 = 6\text{ m}\Omega$

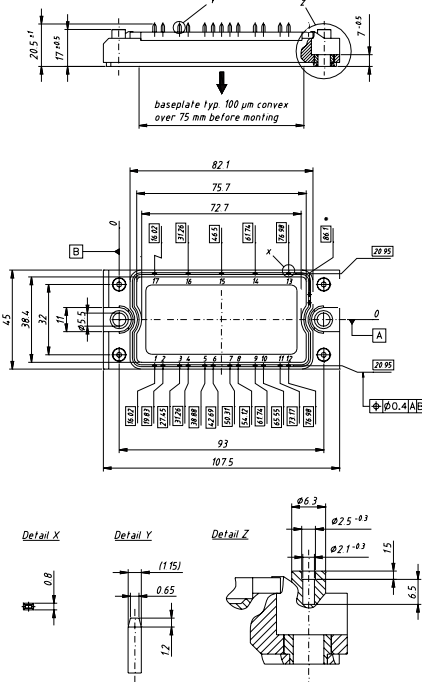
Thermal Response



IGBT (typ.)
 $C_{th1} = 0.22\text{ J/K}; R_{th1} = 0.26\text{ K/W}$
 $C_{th2} = 1.74\text{ J/K}; R_{th2} = 0.09\text{ K/W}$

Free Wheeling Diode (typ.)
 $C_{th1} = 0.151\text{ J/K}; R_{th1} = 0.483\text{ K/W}$
 $C_{th2} = 1.003\text{ J/K}; R_{th2} = 0.127\text{ K/W}$

Dimensions in mm (1 mm = 0.0394")



pins 5, 6, 7, 8 and 15 for MWI only